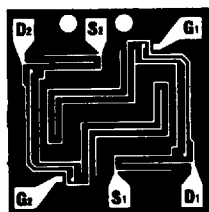


PRODUCT CATALOG

N-CHANNEL DUAL JUNCTION FET

CHIP NUMBER

DMN113.3



.038"
(0.965mm)

.038"
(0.965mm)

Die Size: 38 x 38 (mils)
0.965 x 0.965(mm)
3.5 x 3.5(mils)
Pad Size: 0.089 x 0.089(mm)

CONTACT METALLIZATION

Top Contact: > 12,000
Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

It is advisable that:

- the die be eutectically mounted with gold silicon preform 98/2%.
- 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BVGSS	-30	-50	-60	V	$I_D = 1\mu A, V_{DS} = 0$
I_{GSS}		30	200	pA	$V_{DS} = 0, V_{GS} = -20V$
I_{DSS}	1	6	15	mA	$V_{DS} = 15V, V_{GS} = 0$
V_p	-.5	-2	-4	V	$V_{DS} = 15V, I_D = 1nA$
g_{fs}	1000		8000	μS	$V_{DS} = 15V, V_{GS} = 0, f = 1KHz$
γ_{OS}			10	mho	$V_{DS} = 15V, I_{DG} = 700\mu A$
C_{iss}		16	18	pF	$V_{DS} = 15V, V_{GS} = 0, f = 1MHz$
C_{rss}		5	6	pF	$V_{DS} = 15V, V_{GS} = 0, f = 1MHz$

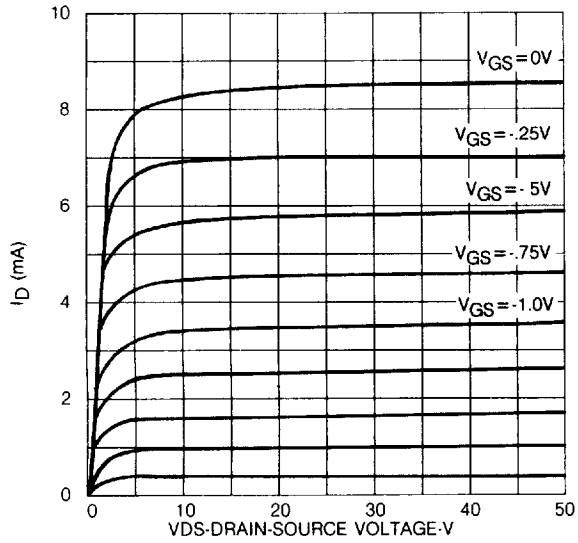
TYPICAL DEVICE TYPES: 2N3921 - 2N3922, 2N4084, 2N4085, SU2365 - SU2369, SU2080, SU2081

PRODUCT CATALOG

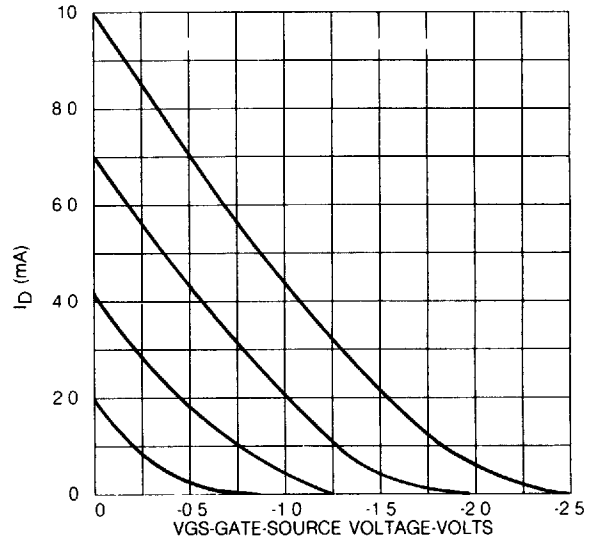
N-CHANNEL DUAL JUNCTION FET

CHIP TYPE DMN113.3

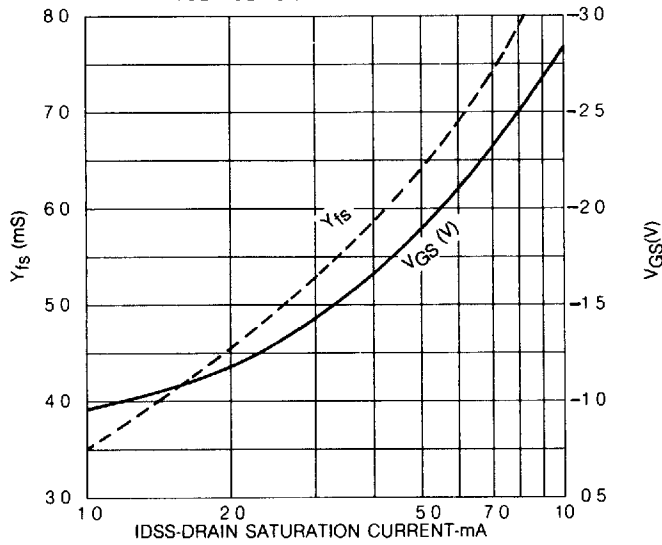
COMMON DRAIN-SOURCE
CHARACTERISTICS



DRAIN CURRENT VS
GATE-SOURCE VOLTAGE



TRANSADMITTANCE/CUT-OFF
VOLTAGE VS DRAIN CURRENT



FORWARD TRANSADMITTANCE
VS DRAIN CURRENT

